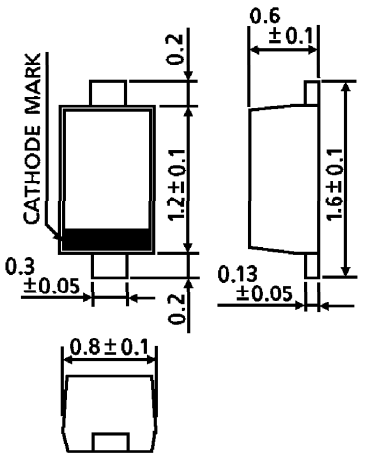
TOSHIBA DIODE SILICON EPITAXIAL PIN TYPE

JDP2S04E

VHF~UHF BAND RF ATTENUATOR APPLICATIONS

Unit in mm

- Suitable for reducing set's size as a result from enabling high-density mounting due to 2-pin small packages.
- Low Capacitance Ratio : C_T = 0.25 pF (Typ.)
- Low Series Resistance : r_s = 3 Ω (Typ.)



ESC	
JEDEC	—
EIAJ	—
TOSHIBA	1-1G1A

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Reverse Voltage	V_R	50	V
Foward Current	I_F	50	mA
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	−55~125	°C

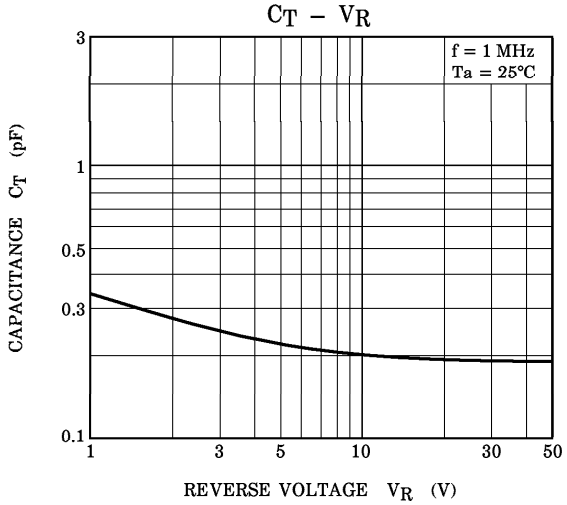
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

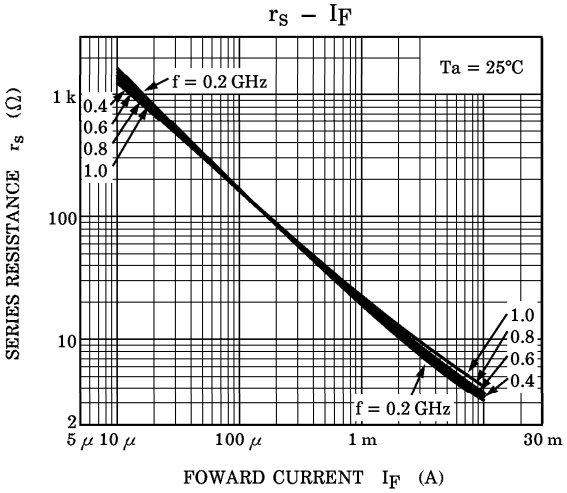
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Voltage	V_R	I_R = 10 μA	50	—	—	V
Reverse Current	I_R	V_R = 50 V	—	—	0.1	μA
Forward Voltage	V_F	I_F = 50 mA	—	0.95	1.0	V
Capacitance	C_T	V_R = 50 V, f = 1 MHz	—	0.25	0.4	pF
Series Resistance	r_s	I_F = 10 mA, f = 100 MHz	—	3.0	—	Ω

* Signal level when capacitance is measured : Vsig = 20 mV_{rms}

MARKING

961001EAA1


$C_T - V_R$
f = 1 MHz
Ta = 25°C
CAPACITANCE C_T (pF)
3
1
0.5
0.3
0.1
1
3
5
10
30
50
REVERSE VOLTAGE V_R (V)


$r_S - I_F$
Ta = 25°C
f = 0.2 GHz
SERIES RESISTANCE r_S (Ω)
1 k
100
10
2
0.4
0.6
0.8
1.0
1.0
0.8
0.6
0.4
f = 0.2 GHz
5 μ
10 μ
100 μ
1 m
30 m
FOWARD CURRENT I_F (A)